



# BFU550

NPN wideband silicon RF transistor

Rev. 2.1 — 17 April 2019

Product data sheet

## 1 Product profile

### 1.1 General description

NPN silicon RF transistor for high speed, low noise applications in a plastic, 4-pin dual-emitter SOT143B package.

The BFU550 is part of the BFU5 family of transistors, suitable for small signal to medium power applications up to 2 GHz.

### 1.2 Features and benefits

- Low noise, high breakdown RF transistor
- AEC-Q101 qualified
- Minimum noise figure ( $NF_{min}$ ) = 0.7 dB at 900 MHz
- Maximum stable gain 21 dB at 900 MHz
- 11 GHz  $f_T$  silicon technology

### 1.3 Applications

- Applications requiring high supply voltages and high breakdown voltages
- Broadband amplifiers up to 2 GHz
- Low noise amplifiers for ISM applications
- ISM band oscillators

### 1.4 Quick reference data

Table 1. Quick reference data

$T_{amb} = 25\text{ °C}$  unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CB}$	collector-base voltage	open emitter	-	-	24	V
$V_{CE}$	collector-emitter voltage	open base	-	-	12	V
		shorted base	-	-	24	V
$V_{EB}$	emitter-base voltage	open collector	-	-	2	V
$I_C$	collector current		-	15	50	mA
$P_{tot}$	total power dissipation	$T_{sp} \leq 87\text{ °C}$	[1]	-	450	mW
$h_{FE}$	DC current gain	$I_C = 15\text{ mA}; V_{CE} = 8\text{ V}$	60	95	200	
$C_c$	collector capacitance	$V_{CB} = 8\text{ V}; f = 1\text{ MHz}$	-	0.72	-	pF
$f_T$	transition frequency	$I_C = 25\text{ mA}; V_{CE} = 8\text{ V}; f = 900\text{ MHz}$	-	11	-	GHz

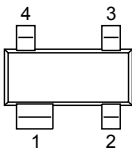
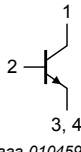


Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$G_{p(max)}$	maximum power gain	$I_C = 15 \text{ mA}; V_{CE} = 8 \text{ V}; f = 900 \text{ MHz}$	[2] -	21	-	dB
$NF_{min}$	minimum noise figure	$I_C = 1 \text{ mA}; V_{CE} = 8 \text{ V}; f = 900 \text{ MHz}; \Gamma_S = \Gamma_{opt}$	-	0.7	-	dB
$P_{L(1dB)}$	output power at 1 dB gain compression	$I_C = 25 \text{ mA}; V_{CE} = 8 \text{ V}; Z_S = Z_L = 50 \Omega; f = 900 \text{ MHz}$	-	13.5	-	dBm

[1]  $T_{sp}$  is the temperature at the solder point of the collector lead.  
 [2] If  $K > 1$  then  $G_{p(max)}$  is the maximum power gain. If  $K < 1$  then  $G_{p(max)} = MSG$ .

## 2 Pinning information

Table 2. Discrete pinning

Pin	Description	Simplified outline	Graphic symbol
1	collector		 aaa-010459
2	base		
3	emitter		
4	emitter		

## 3 Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BFU550	-	plastic surface-mounted package; 4 leads	SOT143B
OM7962	-	Customer evaluation kit for BFU520, BFU530 and BFU550 [1]	-

[1] The customer evaluation kit contains the following:

- Unpopulated RF amplifier Printed-Circuit Board (PCB)
  - Unpopulated RF amplifier Printed-Circuit Board (PCB) with emitter degeneration
    - Four SMA connectors for fitting unpopulated Printed-Circuit Board (PCB)
    - BFU520, BFU530 and BFU550 samples
    - USB stick with data sheets, application notes, models, S-parameter and noise files

## 4 Marking

Table 4. Marking

Type number	Marking	Description
BFU550	*TC	* = t : made in Malaysia
		* = w : made in China

## 5 Design support

**Table 5. Available design support**

Download from the BFU550 product information page on <http://www.nxp.com>.

Support item	Available	Remarks
Device models for Agilent EEsof EDA ADS	yes	Based on Mextram device model.
SPICE model	yes	Based on Gummel-Poon device model.
S-parameters	yes	
Noise parameters	yes	
Customer evaluation kit	yes	See <a href="#">Section 3</a> and <a href="#">Section 10</a> .
Solder pattern	yes	
Application notes	yes	See <a href="#">Section 10.1</a> and <a href="#">Section 10.2</a> .

## 6 Limiting values

**Table 6. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CB}$	collector-base voltage	open emitter	-	30	V
$V_{CE}$	collector-emitter voltage	open base	-	16	V
		shorted base	-	30	V
$V_{EB}$	emitter-base voltage	open collector	-	3	V
$I_C$	collector current		-	80	mA
$T_{stg}$	storage temperature		-65	+150	°C
$V_{ESD}$	electrostatic discharge voltage	Human Body Model (HBM) According to JEDEC standard 22-A114E	-	±150	V
		Charged Device Model (CDM) According to JEDEC standard 22-C101B	-	±2	kV

## 7 Recommended operating conditions

**Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CB}$	collector-base voltage	open emitter	-	-	24	V
$V_{CE}$	collector-emitter voltage	open base	-	-	12	V
		shorted base	-	-	24	V
$V_{EB}$	emitter-base voltage	open collector	-	-	2	V
$I_C$	collector current		-	-	50	mA
$P_i$	input power	$Z_S = 50 \Omega$	-	-	10	dBm
$T_j$	junction temperature		-40	-	+150	°C

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> ≤ 87 °C	[1]	-	450	mW

[1] T<sub>sp</sub> is the temperature at the solder point of the collector lead.

## 8 Thermal characteristics

**Table 8. Thermal characteristics**

Symbol	Parameter	Conditions	Typ	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[1]	140 K/W

[1] T<sub>sp</sub> is the temperature at the solder point of the collector lead.

T<sub>sp</sub> has the following relation to the ambient temperature T<sub>amb</sub>:

$$T_{sp} = T_{amb} + P \times R_{th(sp-a)}$$

With P being the power dissipation and R<sub>th(sp-a)</sub> being the thermal resistance between the solder point and ambient. R<sub>th(sp-a)</sub> is determined by the heat transfer properties in the application.

The heat transfer properties are set by the application board materials, the board layout and the environment e.g. housing.

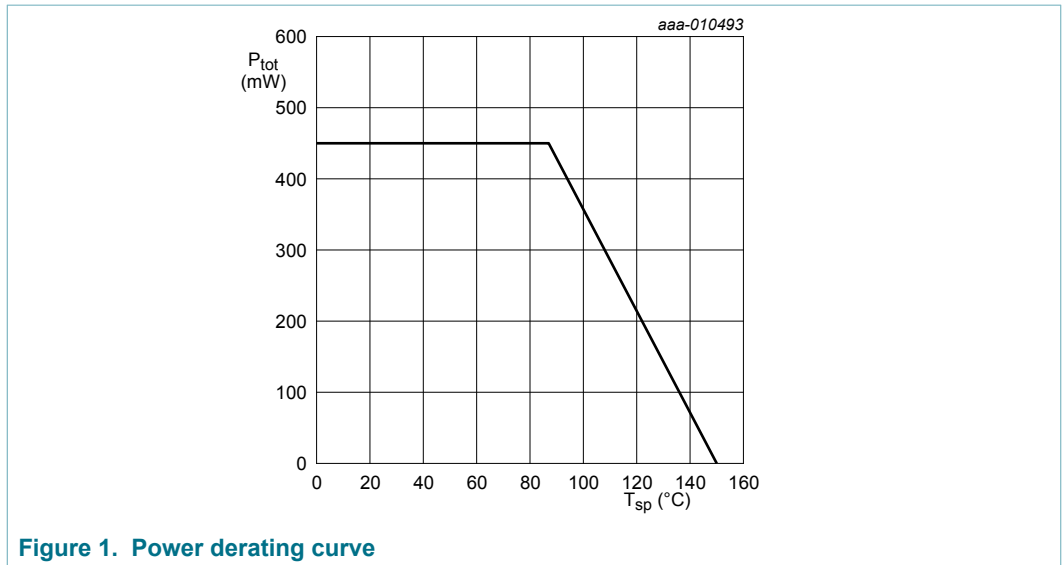


Figure 1. Power derating curve

## 9 Characteristics

**Table 9. Characteristics**

T<sub>amb</sub> = 25 °C unless otherwise specified

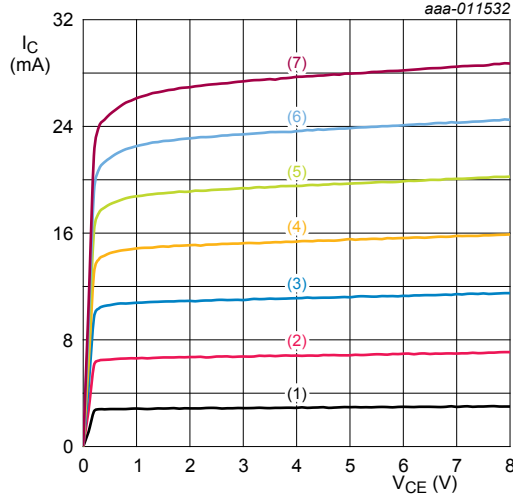
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	I <sub>C</sub> = 100 nA; I <sub>E</sub> = 0 mA	24	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	I <sub>C</sub> = 150 nA; I <sub>B</sub> = 0 mA	12	-	-	V
I <sub>C</sub>	collector current		-	15	50	mA
I <sub>CBO</sub>	collector-base cut-off current	I <sub>E</sub> = 0 mA; V <sub>CB</sub> = 8 V	-	<1	-	nA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$h_{FE}$	DC current gain	$I_C = 15 \text{ mA}; V_{CE} = 8 \text{ V}$	60	95	200	
$C_e$	emitter capacitance	$V_{EB} = 0.5 \text{ V}; f = 1 \text{ MHz}$	-	1.11	-	pF
$C_{re}$	feedback capacitance	$V_{CE} = 8 \text{ V}; f = 1 \text{ MHz}$	-	0.41	-	pF
$C_c$	collector capacitance	$V_{CB} = 8 \text{ V}; f = 1 \text{ MHz}$	-	0.72	-	pF
$f_T$	transition frequency	$I_C = 25 \text{ mA}; V_{CE} = 8 \text{ V}; f = 900 \text{ MHz}$	-	11	-	GHz
$G_{p(max)}$	maximum power gain	$f = 433 \text{ MHz}; V_{CE} = 8 \text{ V}$ [1]				
		$I_C = 1 \text{ mA}$	-	15	-	dB
		$I_C = 15 \text{ mA}$	-	25.5	-	dB
		$I_C = 25 \text{ mA}$	-	26.5	-	dB
		$f = 900 \text{ MHz}; V_{CE} = 8 \text{ V}$ [1]				
		$I_C = 1 \text{ mA}$	-	12.5	-	dB
		$I_C = 15 \text{ mA}$	-	21	-	dB
		$I_C = 25 \text{ mA}$	-	21.5	-	dB
		$f = 1800 \text{ MHz}; V_{CE} = 8 \text{ V}$ [1]				
		$I_C = 1 \text{ mA}$	-	10	-	dB
		$I_C = 15 \text{ mA}$	-	15	-	dB
		$I_C = 25 \text{ mA}$	-	15	-	dB
$ s_{21} ^2$	insertion power gain	$f = 433 \text{ MHz}; V_{CE} = 8 \text{ V}$				
		$I_C = 1 \text{ mA}$	-	10	-	dB
		$I_C = 15 \text{ mA}$	-	23	-	dB
		$I_C = 25 \text{ mA}$	-	23.5	-	dB
		$f = 900 \text{ MHz}; V_{CE} = 8 \text{ V}$				
		$I_C = 1 \text{ mA}$	-	8	-	dB
		$I_C = 15 \text{ mA}$	-	17.5	-	dB
		$I_C = 25 \text{ mA}$	-	18	-	dB
		$f = 1800 \text{ MHz}; V_{CE} = 8 \text{ V}$				
		$I_C = 1 \text{ mA}$	-	4.5	-	dB
		$I_C = 15 \text{ mA}$	-	11.5	-	dB
		$I_C = 25 \text{ mA}$	-	12	-	dB
$NF_{min}$	minimum noise figure	$f = 433 \text{ MHz}; V_{CE} = 8 \text{ V}; \Gamma_S = \Gamma_{opt}$				
		$I_C = 1 \text{ mA}$	-	0.55	-	dB
		$I_C = 15 \text{ mA}$	-	0.9	-	dB
		$I_C = 25 \text{ mA}$	-	1.1	-	dB
		$f = 900 \text{ MHz}; V_{CE} = 8 \text{ V}; \Gamma_S = \Gamma_{opt}$				
		$I_C = 1 \text{ mA}$	-	0.7	-	dB
		$I_C = 15 \text{ mA}$	-	0.95	-	dB
		$I_C = 25 \text{ mA}$	-	1.2	-	dB

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		f = 1800 MHz; V <sub>CE</sub> = 8 V; $\Gamma_S = \Gamma_{opt}$				
		I <sub>C</sub> = 1 mA	-	1	-	dB
		I <sub>C</sub> = 15 mA	-	1.1	-	dB
		I <sub>C</sub> = 25 mA	-	1.3	-	dB
G <sub>ass</sub>	associated gain	f = 433 MHz; V <sub>CE</sub> = 8 V; $\Gamma_S = \Gamma_{opt}$				
		I <sub>C</sub> = 1 mA	-	22.5	-	dB
		I <sub>C</sub> = 15 mA	-	24.5	-	dB
		I <sub>C</sub> = 25 mA	-	25	-	dB
		f = 900 MHz; V <sub>CE</sub> = 8 V; $\Gamma_S = \Gamma_{opt}$				
		I <sub>C</sub> = 1 mA	-	15	-	dB
		I <sub>C</sub> = 15 mA	-	19	-	dB
		I <sub>C</sub> = 25 mA	-	19	-	dB
		f = 1800 MHz; V <sub>CE</sub> = 8 V; $\Gamma_S = \Gamma_{opt}$				
		I <sub>C</sub> = 1 mA	-	9.5	-	dB
		I <sub>C</sub> = 15 mA	-	13	-	dB
		I <sub>C</sub> = 25 mA	-	13.5	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	f = 433 MHz; V <sub>CE</sub> = 8 V; Z <sub>S</sub> = Z <sub>L</sub> = 50 Ω				
		I <sub>C</sub> = 15 mA	-	9.5	-	dBm
		I <sub>C</sub> = 25 mA	-	13.5	-	dBm
		f = 900 MHz; V <sub>CE</sub> = 8 V; Z <sub>S</sub> = Z <sub>L</sub> = 50 Ω				
		I <sub>C</sub> = 15 mA	-	10	-	dBm
		I <sub>C</sub> = 25 mA	-	13.5	-	dBm
		f = 1800 MHz; V <sub>CE</sub> = 8 V; Z <sub>S</sub> = Z <sub>L</sub> = 50 Ω				
		I <sub>C</sub> = 15 mA	-	10	-	dBm
		I <sub>C</sub> = 25 mA	-	13	-	dBm
IP <sub>3o</sub>	output third-order intercept point	f <sub>1</sub> = 433 MHz; f <sub>2</sub> = 434 MHz; V <sub>CE</sub> = 8 V; Z <sub>S</sub> = Z <sub>L</sub> = 50 Ω				
		I <sub>C</sub> = 15 mA	-	19	-	dBm
		I <sub>C</sub> = 25 mA	-	23	-	dBm
		f <sub>1</sub> = 900 MHz; f <sub>2</sub> = 901 MHz; V <sub>CE</sub> = 8 V; Z <sub>S</sub> = Z <sub>L</sub> = 50 Ω				
		I <sub>C</sub> = 15 mA	-	20	-	dBm
		I <sub>C</sub> = 25 mA	-	23	-	dBm
		f <sub>1</sub> = 1800 MHz; f <sub>2</sub> = 1801 MHz; V <sub>CE</sub> = 8 V; Z <sub>S</sub> = Z <sub>L</sub> = 50 Ω				
		I <sub>C</sub> = 15 mA	-	19.5	-	dBm
		I <sub>C</sub> = 25 mA	-	23	-	dBm

[1] If K > 1 then G<sub>p(max)</sub> is the maximum power gain. If K < 1 then G<sub>p(max)</sub> = MSG.

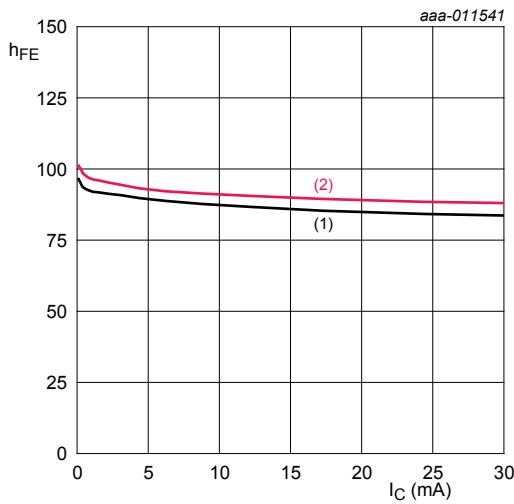
9.1 Graphs



$T_{amb} = 25\text{ }^\circ\text{C}$ .

- 1.  $I_B = 25\text{ }\mu\text{A}$
- 2.  $I_B = 75\text{ }\mu\text{A}$
- 3.  $I_B = 125\text{ }\mu\text{A}$
- 4.  $I_B = 175\text{ }\mu\text{A}$
- 5.  $I_B = 225\text{ }\mu\text{A}$
- 6.  $I_B = 275\text{ }\mu\text{A}$
- 7.  $I_B = 325\text{ }\mu\text{A}$

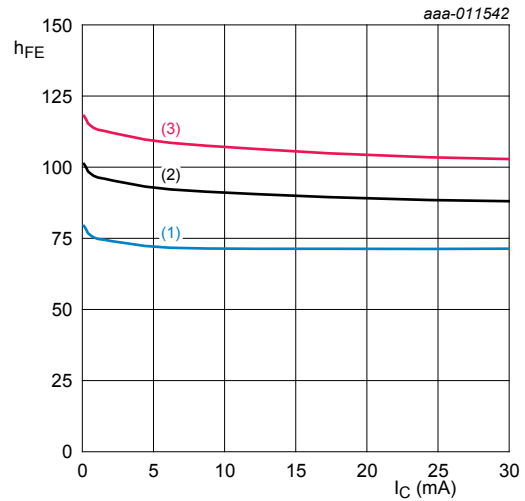
Figure 2. Collector current as a function of collector-emitter voltage; typical values



$T_{amb} = 25\text{ }^\circ\text{C}$ .

- 1.  $V_{CE} = 3.0\text{ V}$
- 2.  $V_{CE} = 8.0\text{ V}$

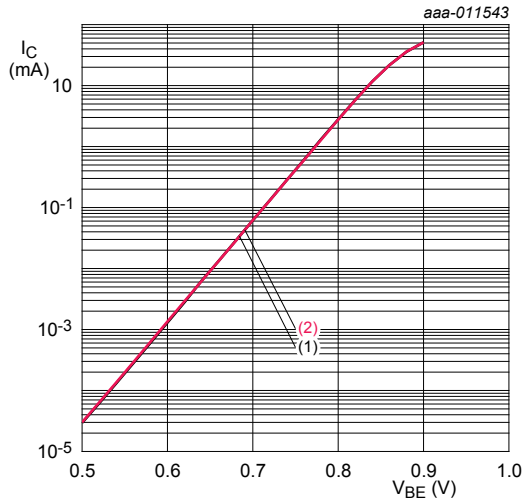
Figure 3. DC current gain as function of collector current; typical values



$V_{CE} = 8\text{ V}$ .

- 1.  $T_{amb} = -40\text{ }^\circ\text{C}$
- 2.  $T_{amb} = +25\text{ }^\circ\text{C}$
- 3.  $T_{amb} = +125\text{ }^\circ\text{C}$

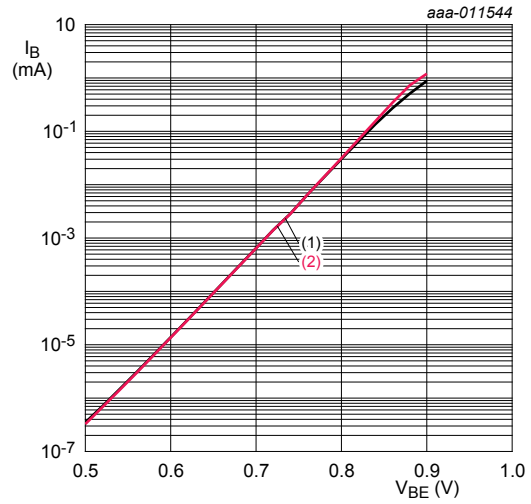
Figure 4. DC current gain as function of collector current; typical values



$T_{amb} = 25\text{ }^{\circ}\text{C}$ .

1.  $V_{CE} = 3.0\text{ V}$
2.  $V_{CE} = 8.0\text{ V}$

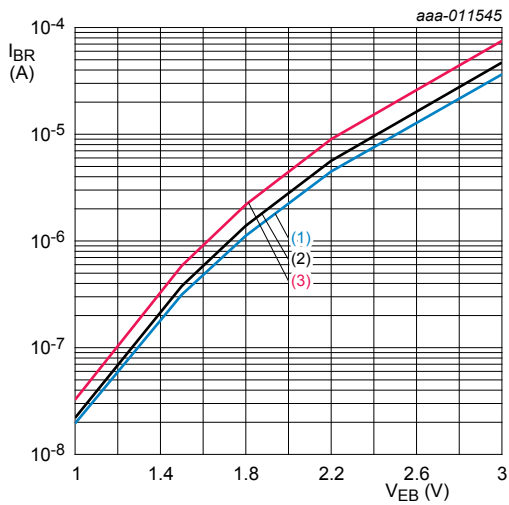
**Figure 5. Collector current as a function of base-emitter voltage; typical values**



$T_{amb} = 25\text{ }^{\circ}\text{C}$ .

1.  $V_{CE} = 3.0\text{ V}$
2.  $V_{CE} = 8.0\text{ V}$

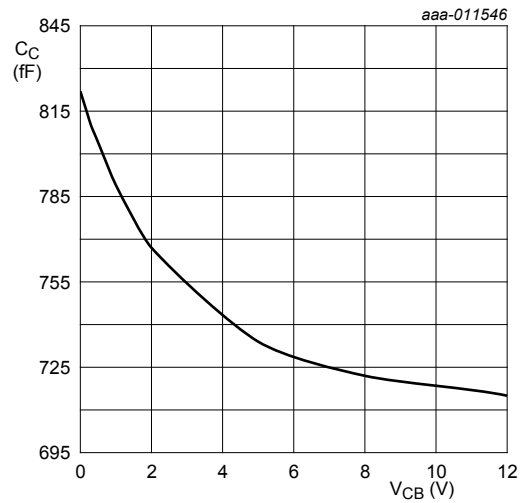
**Figure 6. Base current as a function of base-emitter voltage; typical values**



$V_{CE} = 3\text{ V}$ .

1.  $T_{amb} = -40\text{ }^{\circ}\text{C}$
2.  $T_{amb} = +25\text{ }^{\circ}\text{C}$
3.  $T_{amb} = +125\text{ }^{\circ}\text{C}$

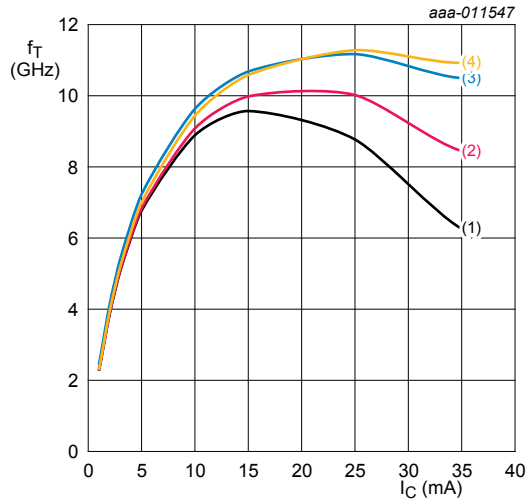
**Figure 7. Reverse base current as a function of emitter-base voltage; typical values**



$I_C = 0\text{ mA}$ ;  $f = 1\text{ MHz}$ ;  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .

**Figure 8. Collector capacitance as a function of collector-base voltage; typical values**

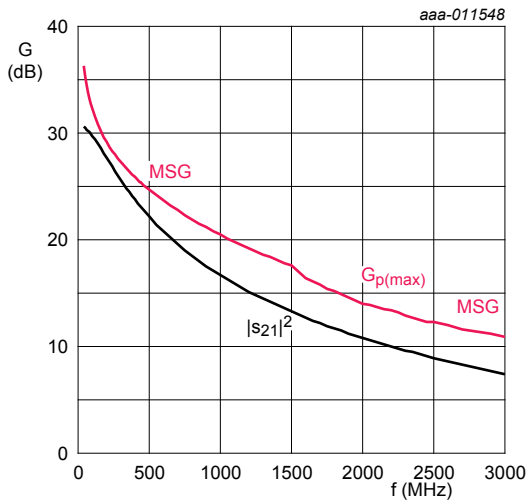




$T_{amb} = 25\text{ }^\circ\text{C}$ .

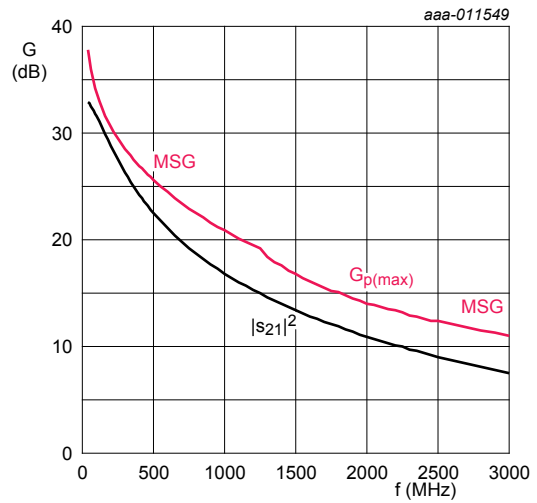
1.  $V_{CE} = 3.3\text{ V}$
2.  $V_{CE} = 5.0\text{ V}$
3.  $V_{CE} = 8.0\text{ V}$
4.  $V_{CE} = 12.0\text{ V}$

Figure 9. Transition frequency as a function of collector current; typical values



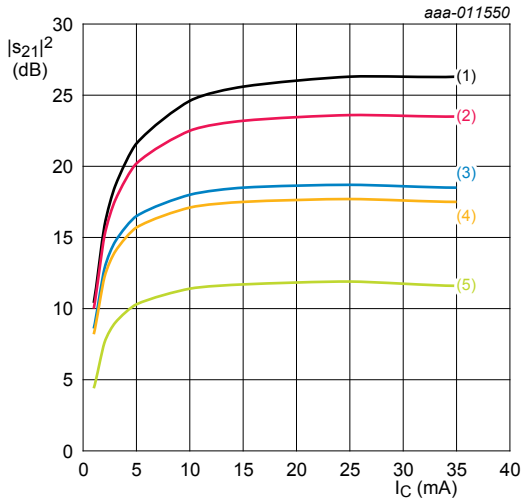
$I_C = 15\text{ mA}$ ;  $V_{CE} = 8\text{ V}$ ;  $T_{amb} = 25\text{ }^\circ\text{C}$ .

Figure 10. Gain as a function of frequency; typical values



$I_C = 25\text{ mA}$ ;  $V_{CE} = 8\text{ V}$ ;  $T_{amb} = 25\text{ }^\circ\text{C}$ .

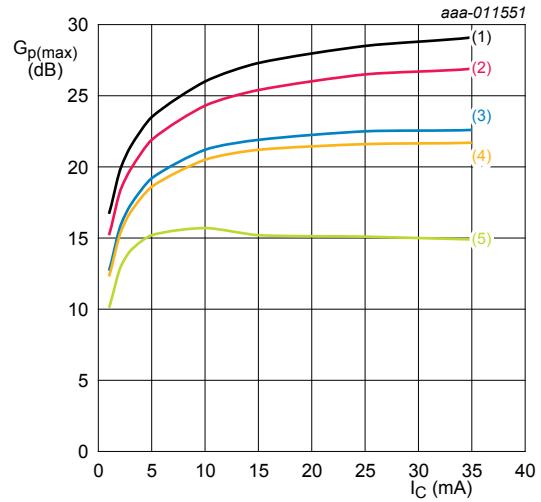
Figure 11. Gain as a function of frequency; typical values



$V_{CE} = 8 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}.$

1.  $f = 300 \text{ MHz}$
2.  $f = 433 \text{ MHz}$
3.  $f = 800 \text{ MHz}$
4.  $f = 900 \text{ MHz}$
5.  $f = 1800 \text{ MHz}$

**Figure 12. Insertion power gain as a function of collector current; typical values**

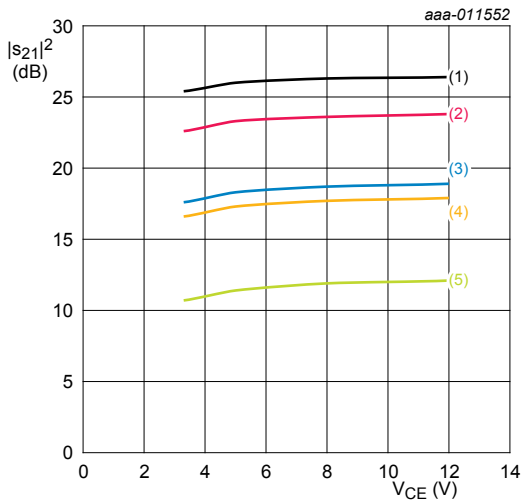


$V_{CE} = 8 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}.$

If  $K > 1$  then  $G_{p(max)}$  = maximum power gain. If  $K < 1$  then  $G_{p(max)}$  = MSG.

1.  $f = 300 \text{ MHz}$
2.  $f = 433 \text{ MHz}$
3.  $f = 800 \text{ MHz}$
4.  $f = 900 \text{ MHz}$
5.  $f = 1800 \text{ MHz}$

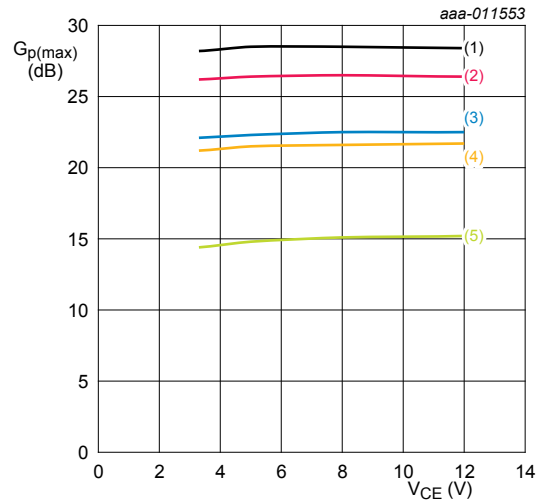
**Figure 13. Maximum power gain as a function of collector current; typical values**



$I_C = 25 \text{ mA}; T_{amb} = 25 \text{ }^\circ\text{C}.$

1.  $f = 300 \text{ MHz}$
2.  $f = 433 \text{ MHz}$
3.  $f = 800 \text{ MHz}$
4.  $f = 900 \text{ MHz}$
5.  $f = 1800 \text{ MHz}$

**Figure 14. Insertion power gain as a function of collector-emitter voltage; typical values**

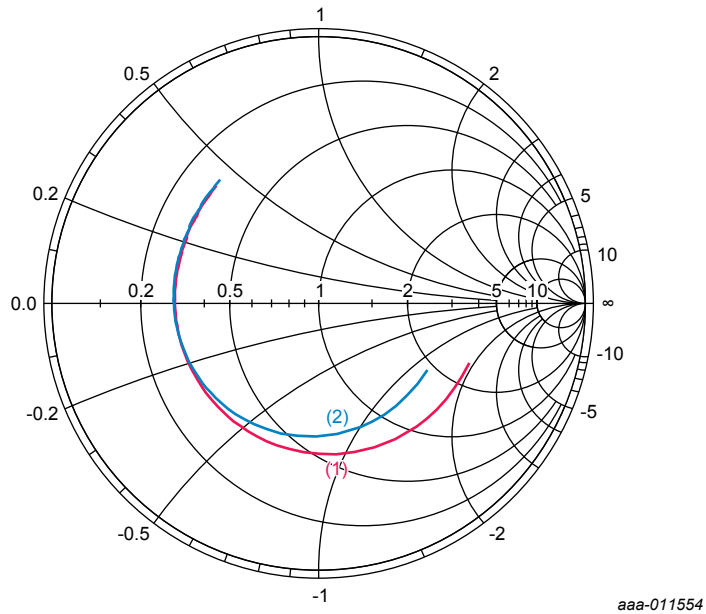


$I_C = 25 \text{ mA}; T_{amb} = 25 \text{ }^\circ\text{C}.$

If  $K > 1$  then  $G_{p(max)}$  = maximum power gain. If  $K < 1$  then  $G_{p(max)}$  = MSG.

1.  $f = 300 \text{ MHz}$
2.  $f = 433 \text{ MHz}$
3.  $f = 800 \text{ MHz}$
4.  $f = 900 \text{ MHz}$
5.  $f = 1800 \text{ MHz}$

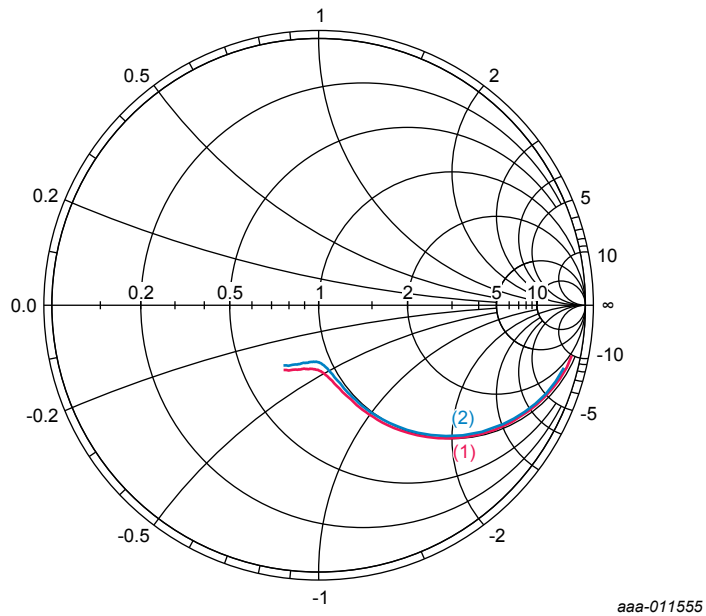
**Figure 15. Maximum power gain as a function of collector-emitter voltage; typical values**



$V_{CE} = 8\text{ V}$ ;  $40\text{ MHz} \leq f \leq 3\text{ GHz}$ .

1.  $I_C = 15\text{ mA}$
2.  $I_C = 25\text{ mA}$

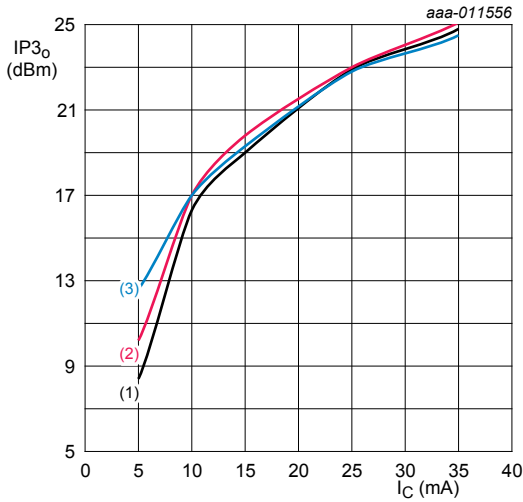
**Figure 16. Input reflection coefficient ( $s_{11}$ ); typical values**



$V_{CE} = 8\text{ V}$ ;  $40\text{ MHz} \leq f \leq 3\text{ GHz}$ .

1.  $I_C = 15\text{ mA}$
2.  $I_C = 25\text{ mA}$

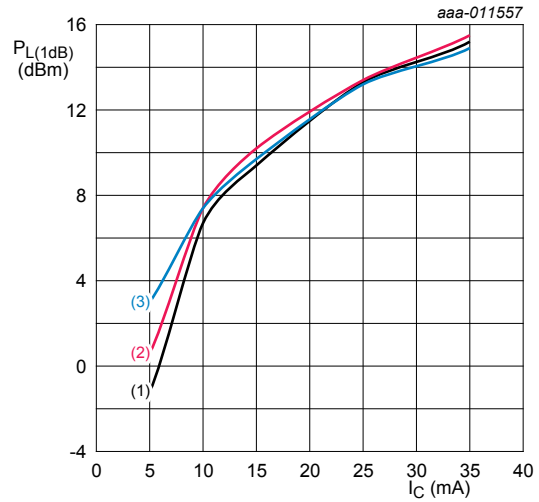
**Figure 17. Output reflection coefficient ( $s_{22}$ ); typical values**



$V_{CE} = 8\text{ V}$ ;  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .

1.  $f_1 = 433\text{ MHz}$ ;  $f_2 = 434\text{ MHz}$
2.  $f_1 = 900\text{ MHz}$ ;  $f_2 = 901\text{ MHz}$
3.  $f_1 = 1800\text{ MHz}$ ;  $f_2 = 1801\text{ MHz}$

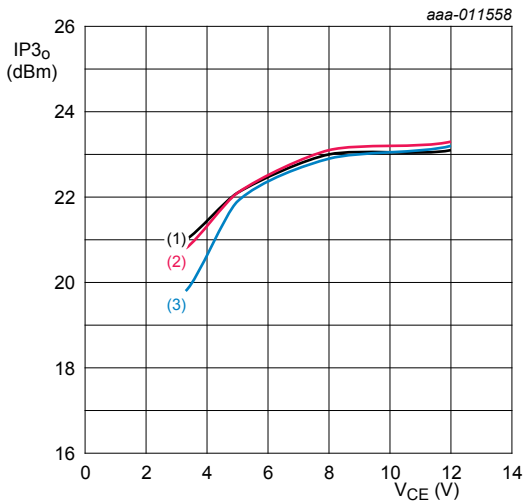
**Figure 18. Output third-order intercept point as a function of collector current; typical values**



$V_{CE} = 8\text{ V}$ ;  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .

1.  $f = 433\text{ MHz}$
2.  $f = 900\text{ MHz}$
3.  $f = 1800\text{ MHz}$

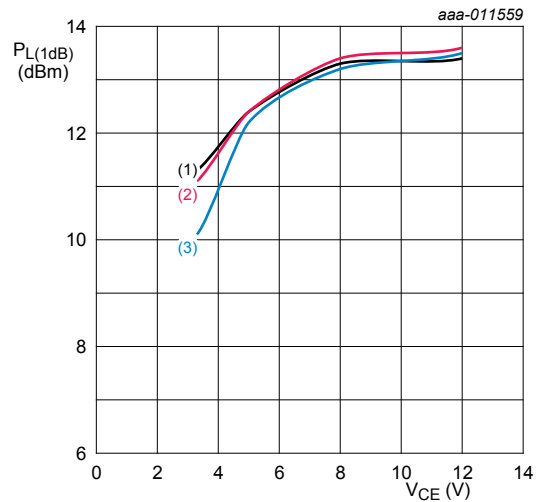
**Figure 19. Output power at 1 dB gain compression as a function of collector current; typical values**



$I_C = 25\text{ mA}$ ;  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .

1.  $f_1 = 433\text{ MHz}$ ;  $f_2 = 434\text{ MHz}$
2.  $f_1 = 900\text{ MHz}$ ;  $f_2 = 901\text{ MHz}$
3.  $f_1 = 1800\text{ MHz}$ ;  $f_2 = 1801\text{ MHz}$

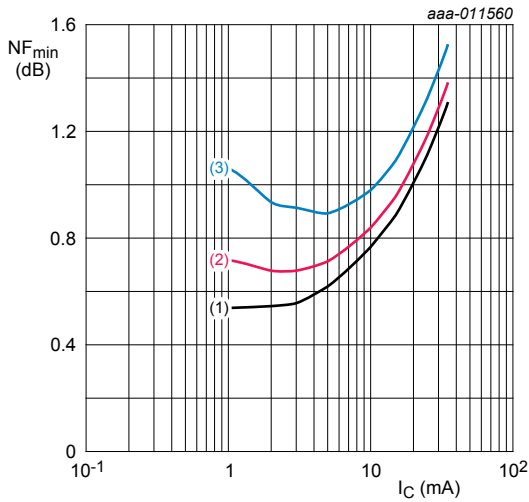
**Figure 20. Output third-order intercept point as a function of collector-emitter voltage; typical values**



$I_C = 25\text{ mA}$ ;  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .

1.  $f = 433\text{ MHz}$
2.  $f = 900\text{ MHz}$
3.  $f = 1800\text{ MHz}$

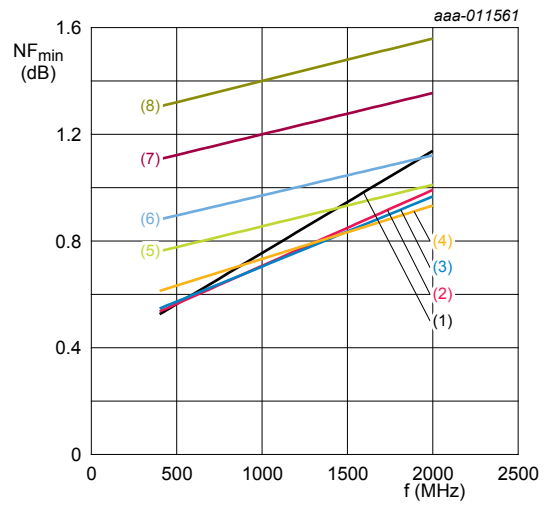
**Figure 21. Output power at 1 dB gain compression as a function of collector-emitter voltage; typical values**



$V_{CE} = 8\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}; \Gamma_S = \Gamma_{opt}$

1.  $f = 433\text{ MHz}$
2.  $f = 900\text{ MHz}$
3.  $f = 1800\text{ MHz}$

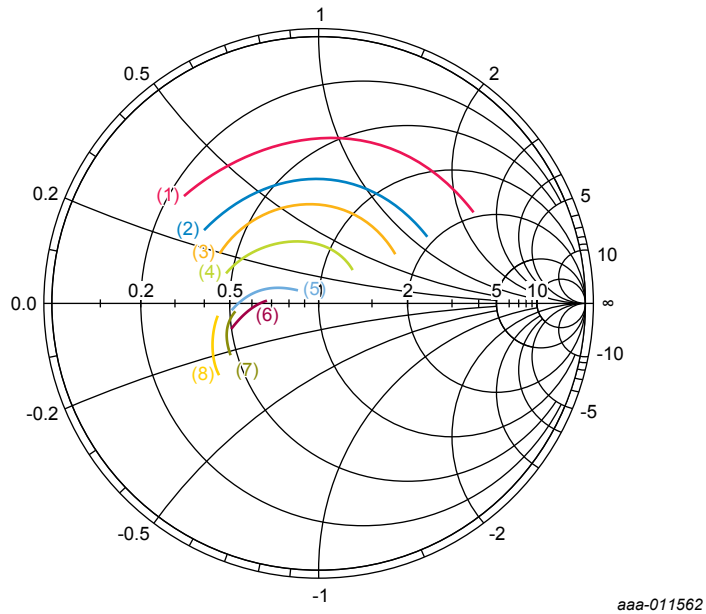
**Figure 22. Minimum noise figure as a function of collector current; typical values**



$V_{CE} = 8\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}; \Gamma_S = \Gamma_{opt}$

1.  $I_C = 1\text{ mA}$
2.  $I_C = 2\text{ mA}$
3.  $I_C = 3\text{ mA}$
4.  $I_C = 5\text{ mA}$
5.  $I_C = 10\text{ mA}$
6.  $I_C = 15\text{ mA}$
7.  $I_C = 25\text{ mA}$
8.  $I_C = 35\text{ mA}$

**Figure 23. Minimum noise figure as a function of frequency; typical values**



$V_{CE} = 8\text{ V}; 400\text{ MHz} \leq f \leq 2\text{ GHz}.$

1.  $I_C = 1\text{ mA}$
2.  $I_C = 2\text{ mA}$
3.  $I_C = 3\text{ mA}$
4.  $I_C = 5\text{ mA}$
5.  $I_C = 10\text{ mA}$
6.  $I_C = 15\text{ mA}$
7.  $I_C = 25\text{ mA}$
8.  $I_C = 35\text{ mA}$

**Figure 24. Optimum reflection coefficient ( $\Gamma_{opt}$ ); typical values**

## 10 Application information

More information about the following application example can be found in the application notes. See [Section 5 "Design support"](#).

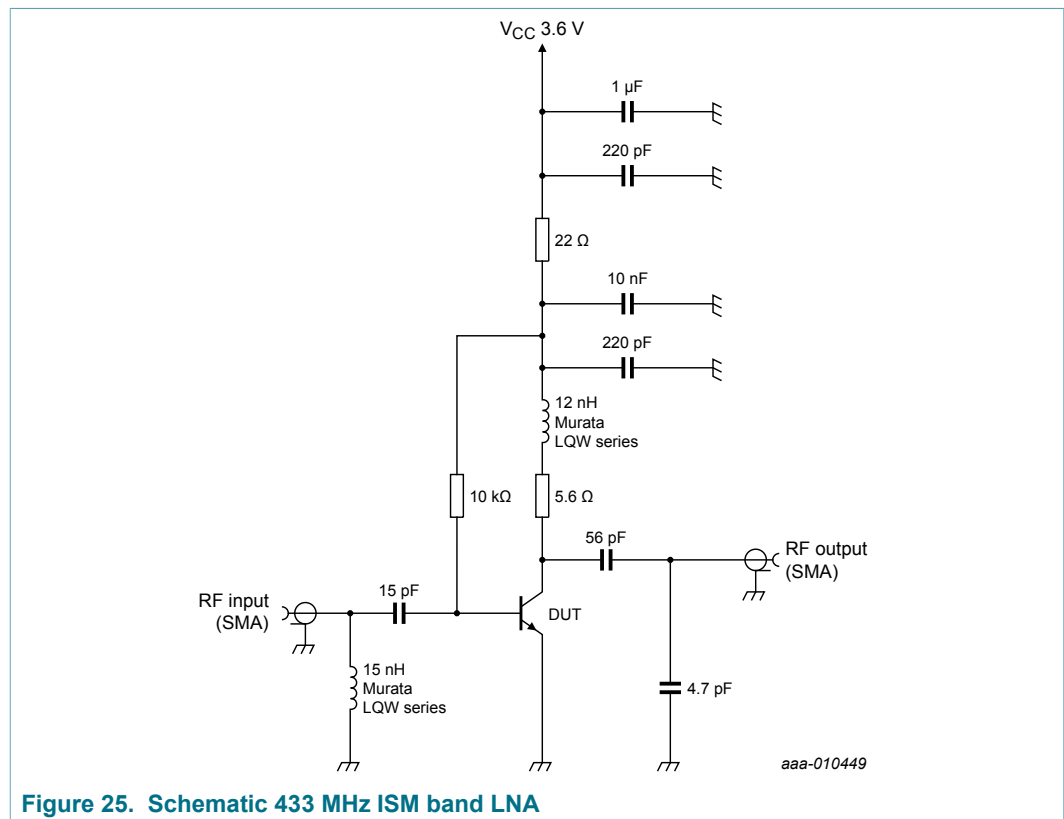
The following application example can be implemented using the evaluation kit. See [Section 3 "Ordering information"](#) for the order type number.

The following application example can be simulated using the simulation package. See [Section 5 "Design support"](#).

### 10.1 Application example: 433 ISM band LNA

433 ISM band LNA, optimized for low noise.

More detailed information of the application example can be found in the application note: [AN11431](#).



**Figure 25. Schematic 433 MHz ISM band LNA**

Remark: fine tuning of components may be required depending on PCB parasitics.

**Table 10. Application performance data at 433 MHz**

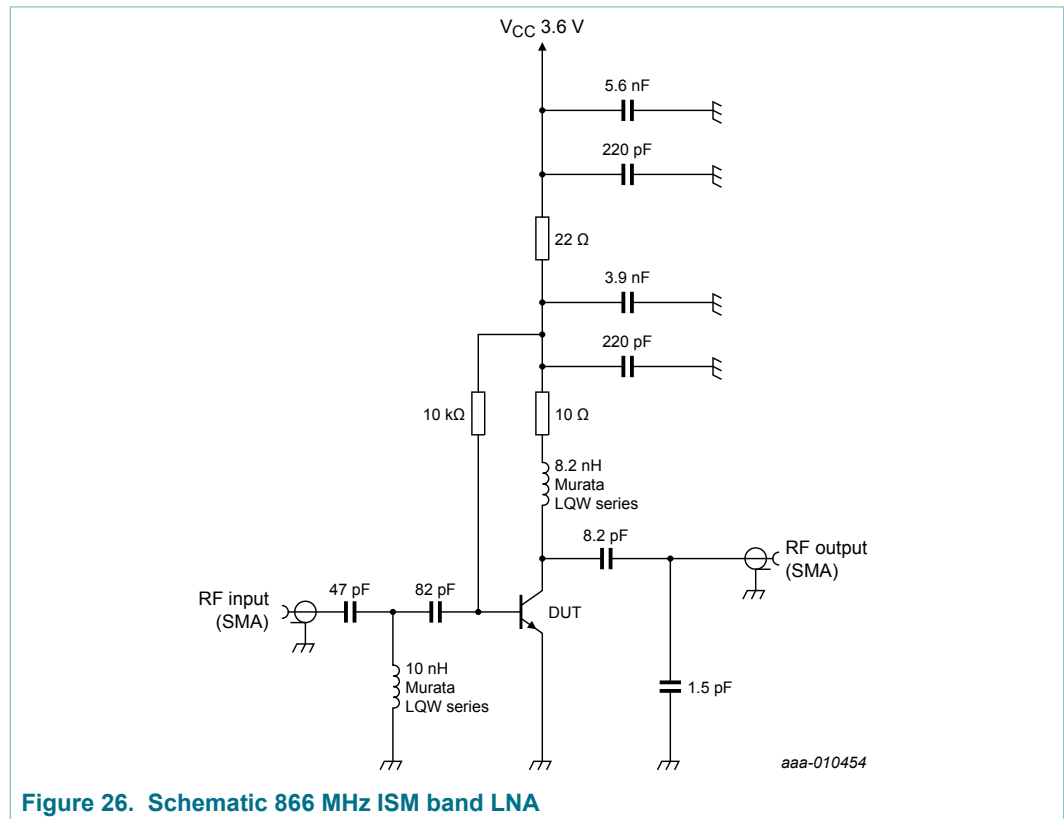
$I_{CC} = 20 \text{ mA}$ ;  $V_{CC} = 3.6 \text{ V}$

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$ s_{21} ^2$	insertion power gain		-	21	-	dB
NF	noise figure		-	1.3	-	dB
IP <sub>3o</sub>	output third-order intercept point	$f_1 = 433.1 \text{ MHz}$ ; $f_2 = 433.2 \text{ MHz}$ ; $P_1 = -30 \text{ dBm per carrier}$	-	19	-	dBm

**10.2 Application example: 866 ISM band LNA**

866 ISM band LNA, optimized for low noise.

More detailed information of the application example can be found in the application note: AN11432.



**Figure 26. Schematic 866 MHz ISM band LNA**

Remark: fine tuning of components maybe required depending on PCB parasitics.

**Table 11. Application performance data at 866 MHz**

$I_{CC} = 20 \text{ mA}$ ;  $V_{CC} = 3.6 \text{ V}$

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$ S_{21} ^2$	insertion power gain		-	15	-	dB
NF	noise figure		-	1.4	-	dB
IP3 <sub>o</sub>	output third-order intercept point	$f_1 = 866.1 \text{ MHz}$ ; $f_2 = 866.2 \text{ MHz}$ ; $P_1 = -30 \text{ dBm}$ per carrier	-	19	-	dBm



**11 Package outline**

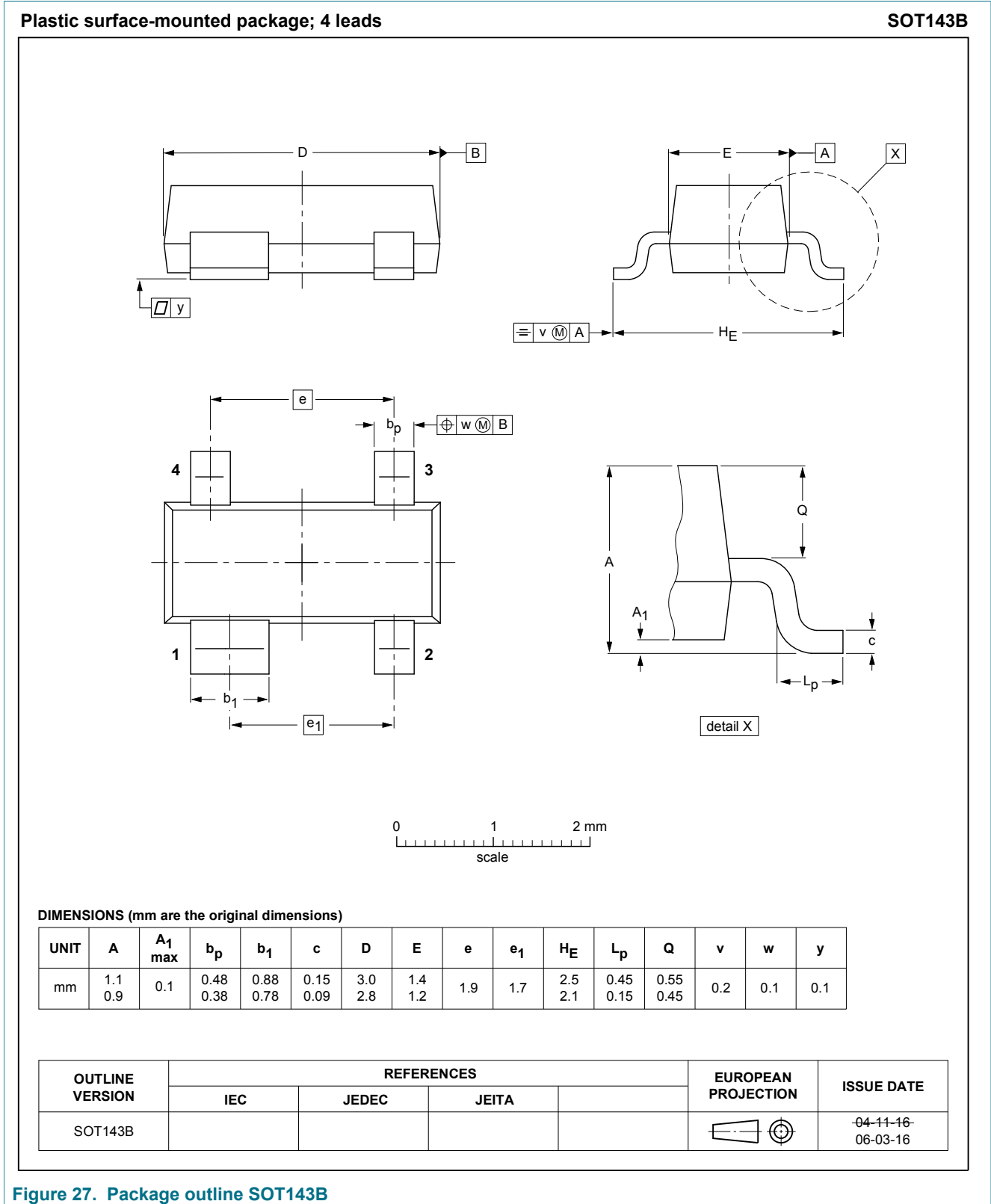


Figure 27. Package outline SOT143B

## 12 Handling information

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices. Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

## 13 Abbreviations

Table 12. Abbreviations

Acronym	Description
AEC	automotive electronics council
ISM	industrial, scientific, and medical
LNA	low-noise amplifier
MSG	maximum stable gain
NPN	negative-positive-negative
SMA	SubMiniature version A

## 14 Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BFU550 v.2.1	20190417	Product data sheet	-	BFU550 v.2
modification	<ul style="list-style-type: none"> <li>Extended the description on the changes in Schematic 866 MHz ISM band LNA: Biasing on the schematic is adapted according to the EVB to do the RF/DC. Connection of 10 K resistor moved to the other side of the 82 pF capacitor</li> </ul>			
BFU550 v.2	20190408	Product data sheet	-	BFU550 v.1
modification	<ul style="list-style-type: none"> <li>Adapted Schematic 866 MHz ISM band LNA.</li> </ul>			
BFU550 v.1	20140305	Product data sheet	-	-

## 15 Legal information

### 15.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[2] The term 'short data sheet' is explained in section "Definitions".

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